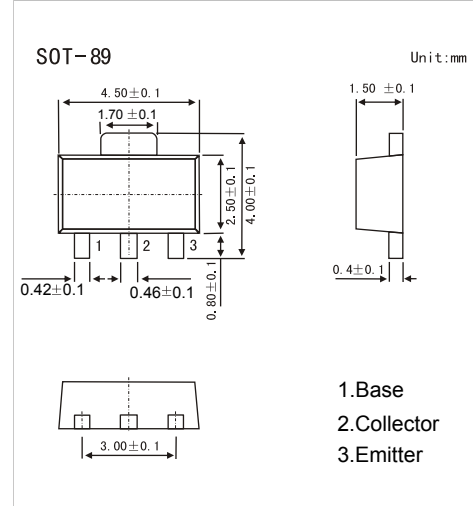


PNP Transistors

2SB804

■ Features

- World standard miniature package: SOT-89
- High collector to base voltage: $V_{CB0} > -100V$
- Excell DC Current gain linearity.



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-100	V
Collector - Emitter Voltage	V_{CE0}	-80	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_c	-1.0	A
Collector Current -Pulse *		-1.5	
Collector Power Dissipation	P_c	2.0	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

* $PW \leq 10$ ms, duty cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = -100 \mu A, I_E = 0$	-100			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = -1$ mA, $I_b = 0$	-80			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_c = 0$	-5			
Collector cutoff current	I_{CB0}	$V_{CB} = -100V, I_E = 0$			-100	nA
Emitter cutoff current	I_{EB0}	$V_{EB} = -5V, I_c = 0$			-100	
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_c = -500$ mA, $I_b = -50$ mA		-0.29	-0.5	V
Base - emitter saturation voltage *1	$V_{BE(sat)}$	$I_c = -500$ mA, $I_b = -50$ mA		-0.9	-1.5	
Base - emitter voltage *1	V_{BE}	$V_{CE} = -10V, I_c = -10$ mA	-600	-840	-700	
DC current gain *1	$h_{FE(1)}$	$V_{CE} = -2.0V, I_c = -100$ mA	90	200	400	
	$h_{FE(2)}$	$V_{CE} = -2.0V, I_c = -500$ mA	25	80		
Collector output capacitance	C_{ob}	$V_{CE} = -5.0V, I_E = 0$		26		pF
Transition frequency	f_T	$V_{CE} = -10V, I_E = 0, f = 1$ MHz		80		MHz

*1 Pulsed: $PW \leq 350 \mu s$, duty cycle $\leq 2\%$

■ Classification of $h_{FE(1)}$

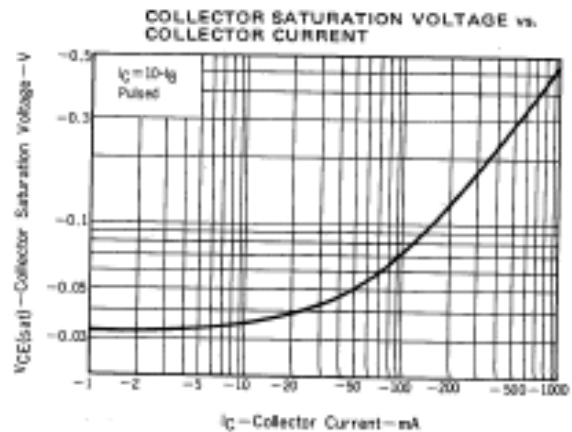
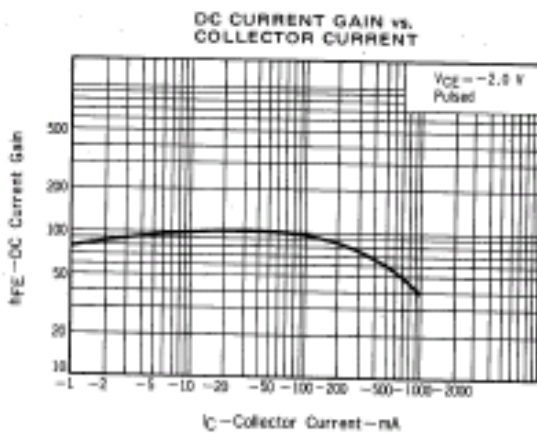
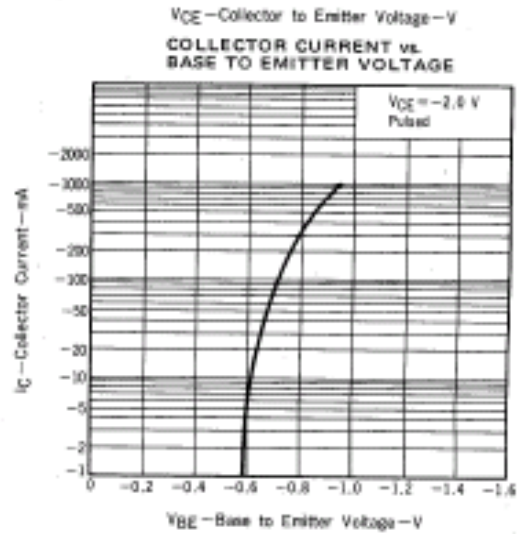
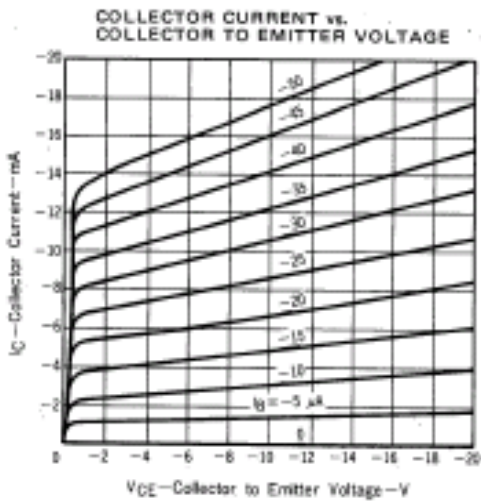
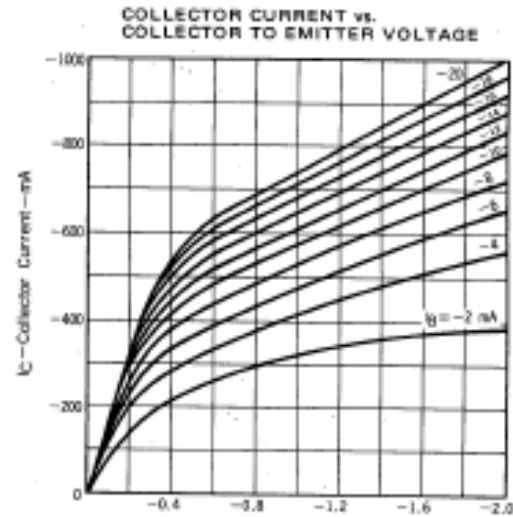
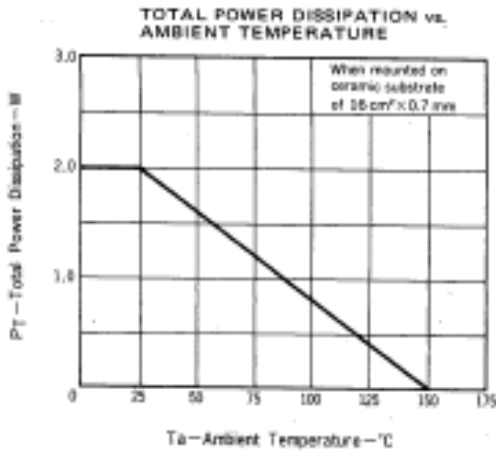
Marking	AW	AV	AU
h_{FE}	90~180	135~270	200~400



炬芯微
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PNP Transistors 2SB804

■ Typical Characteristics



PNP Transistors

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■ Typical Characteristics

